

16K x 4 Static RAM

L7C161/162

FEATURES

- ❑ 16K x 4 Static RAM with Separate I/O, Transparent Write (L7C161), or High Impedance Write (L7C162)
- ❑ Auto-Powerdown™ Design
- ❑ Advanced CMOS Technology
- ❑ High Speed — to 8 ns maximum
- ❑ Low Power Operation
Active: 210 mW typical at 35 ns
Standby: 500 μW typical
- ❑ Data Retention at 2 V for Battery Backup Operation
- ❑ Plug Compatible with IDT 71981/71982, Cypress CY7C161/162
- ❑ Package Styles Available:
 - 28-pin Plastic DIP
 - 28-pin Sidebrazed, Hermetic DIP
 - 28-pin CerDIP
 - 28-pin Plastic SOIC
 - 28-pin Plastic SOJ
 - 28-pin Ceramic LCC

DESCRIPTION

The L7C161 and L7C162 are high-performance, low-power CMOS static RAMs. The storage cells are organized as 16,384 words by 4 bits per word. Data In and Data Out are separate. These devices are available in seven speeds with maximum access times from 8 ns to 35 ns.

Inputs and output are TTL compatible. Operation is from a single +5 V power supply. Power consumption is 210 mW (typical) at 35 ns. Dissipation drops to 75 mW (typical) when the memory is deselected (Enable is high).

Two standby modes are available. Proprietary Auto-Powerdown™ circuitry reduces power consumption automatically during read or write accesses which are longer than the minimum access time, or when the

memory is deselected. In addition, data may be retained in inactive storage with a supply voltage as low as 2 V. The L7C161 and L7C162 consume only 30 μW (typical) at 3 V, allowing effective battery backup operation.

The L7C161 and L7C162 provide asynchronous (unlocked) operation with matching access and cycle times. Two active-low Chip Enables and a three-state bus output with a separate Output Enable control simplify the connection of several chips for increased storage capacity.

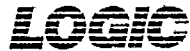
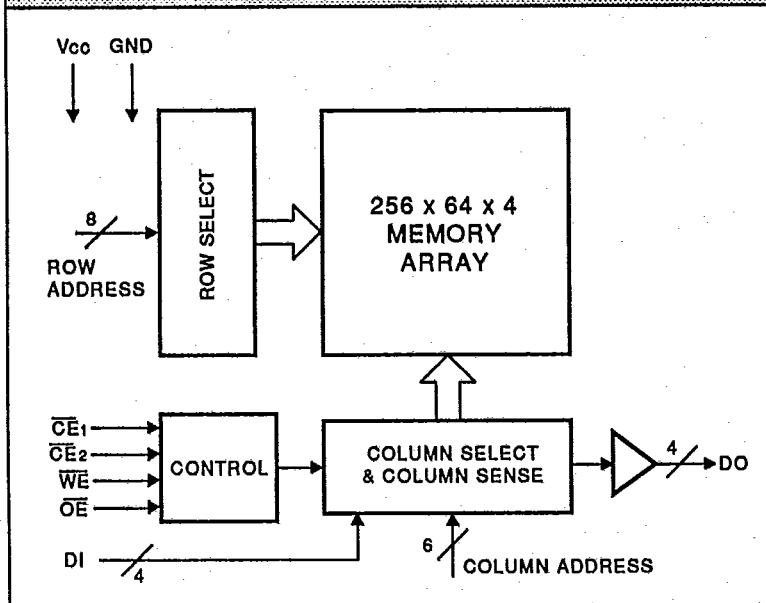
Memory locations are specified on address pins A0 through A13. Reading from a designated location is accomplished by presenting an address and driving $\overline{CE1}$ and $\overline{CE2}$ low while \overline{WE} remains high. The data in the addressed memory location will then appear on the Data Out pins within one access time. The output pins stay in a high-impedance state when \overline{WE} is low (L7C162 only) or $\overline{CE1}$, $\overline{CE2}$, or \overline{OE} is high.

Writing to an addressed location is accomplished when the active-low $\overline{CE1}$ and $\overline{CE2}$ and \overline{WE} inputs are all low. Any of these signals may be used to terminate the write operation. The Data In and Data Out signals have the same polarity.

Latchup and static discharge protection are provided on-chip. The L7C161 and L7C162 can withstand an injection current of up to 200 mA on any pin without damage.

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L7C161/162 Block Diagram



T-46-23-10

MAXIMUM RATINGS Above which useful life may be impaired (Notes 1, 2)

Storage temperature	-65°C to +150°C
Operating ambient temperature	-55°C to +125°C
Vcc supply voltage with respect to ground	-0.5 V to +7.0 V
Input signal with respect to ground	-3.0 V to +7.0 V
Signal applied to high impedance output	-3.0 V to +7.0 V
Output current into low outputs	25 mA
Latchup current	> 200 mA

OPERATING CONDITIONS To meet specified electrical and switching characteristics

Mode	Temperature Range (Ambient)	Supply Voltage
Active Operation, Commercial	0°C to +70°C	4.5 V ≤ Vcc ≤ 5.5 V
Active Operation, Military	-55°C to +125°C	4.5 V ≤ Vcc ≤ 5.5 V
Data Retention, Commercial	0°C to +70°C	2.0 V ≤ Vcc ≤ 5.5 V
Data Retention, Military	-55°C to +125°C	2.0 V ≤ Vcc ≤ 5.5 V

ELECTRICAL CHARACTERISTICS Over Operating Conditions (Note 5)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
VOH	Output High Voltage	IOH = -4.0 mA, Vcc = 4.5 V	2.4			V
VOL	Output Low Voltage	IOL = 8.0 mA			0.4	V
VIH	Input High Voltage		2.0		Vcc + 0.3	V
VIL	Input Low Voltage	(Note 3)	-3.0		0.8	V
IIX	Input Current	GND ≤ VIN ≤ Vcc	-10		+10	μA
IOZ	Output Leakage Current	GND ≤ VOUT ≤ Vcc, CE = Vcc	-10		+10	μA
IOS	Output Short Current	VOUT = GND, Vcc = Max (Note 4)			-350	mA
ICC2	Vcc Current, TTL Inactive	(Note 7)		15	30	mA
ICC3	Vcc Current, CMOS Standby	(Note 8)		100	500	μA
ICC4	Vcc Current, Data Retention	Vcc = 3.0 V (Note 9)		10	250	μA
CIN	Input Capacitance	Ambient Temp = 25°C, Vcc = 5.0 V			5	pF
COU	Output Capacitance	Test Frequency = 1 MHz (Note 10)			7	pF

Symbol	Parameter	Test Condition	L7C161/162-						Unit	
			35	25	20	15	12	10		8
ICC1	Vcc Current, Active	(Note 6)	75	100	125	160	190	205	225	mA



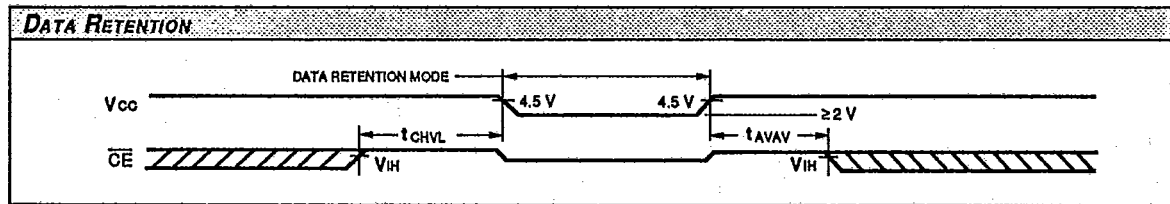
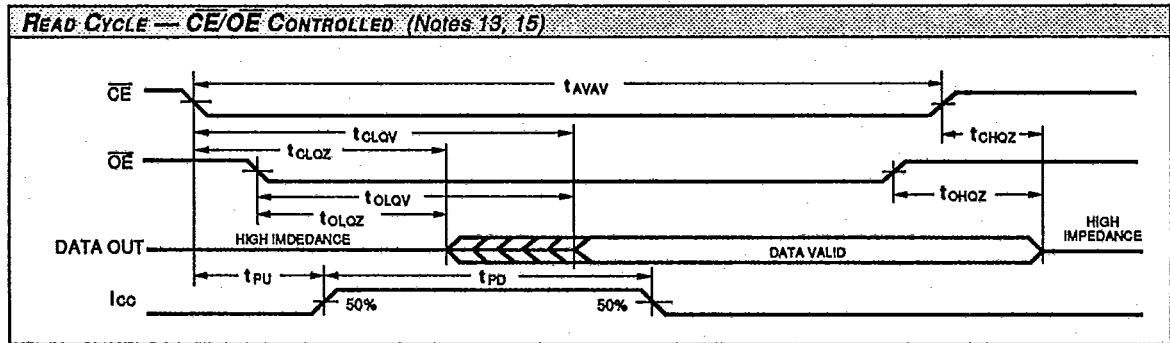
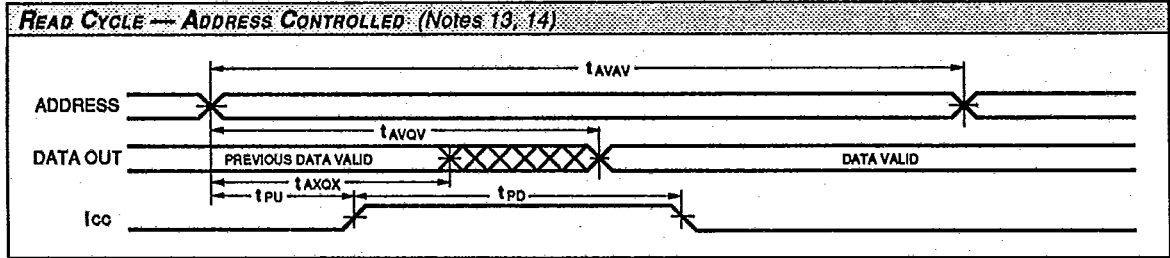
Memory Products

SWITCHING CHARACTERISTICS Over Operating Range (ns)

READ CYCLE (Notes 5, 11, 12, 22, 23, 24)

Symbol	Parameter	L7C161/162-													
		35		25		20		15		12		10		8	
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
tAVAV	Read Cycle Time	35		25		20		15		12		10		8	
tAVQV	Address Valid to Output Valid (13, 14)		35		25		20		15		12		10		8
tAXOX	Address Change to Output Change	3		3		3		3		3		3		3	
tCLOV	Chip Enable Low to Output Valid (13, 15)		35		25		20		15		12		10		8
tCLOZ	Chip Enable Low to Output Low Z (20, 21)	3		3		3		3		3		3		3	
tCHOZ	Chip Enable High to Output High Z (20, 21)		15		10		8		8		5		4		4
tOLOV	Output Enable Low to Output Valid		15		12		10		8		6		5		4
tOLOZ	Output Enable Low to Output Low Z (20, 21)	0		0		0		0		0		0		0	
tOHOZ	Output Enable High to Output High Z (20, 21)		12		10		8		5		5		4		4
tPU	Input Transition to Power Up (10, 19)	0		0		0		0		0		0		0	
tPD	Power Up to Power Down (10, 19)		35		25		20		20		20		18		15
tCHVL	Chip Enable High to Data Retention (10)	0		0		0		0		0		0		0	

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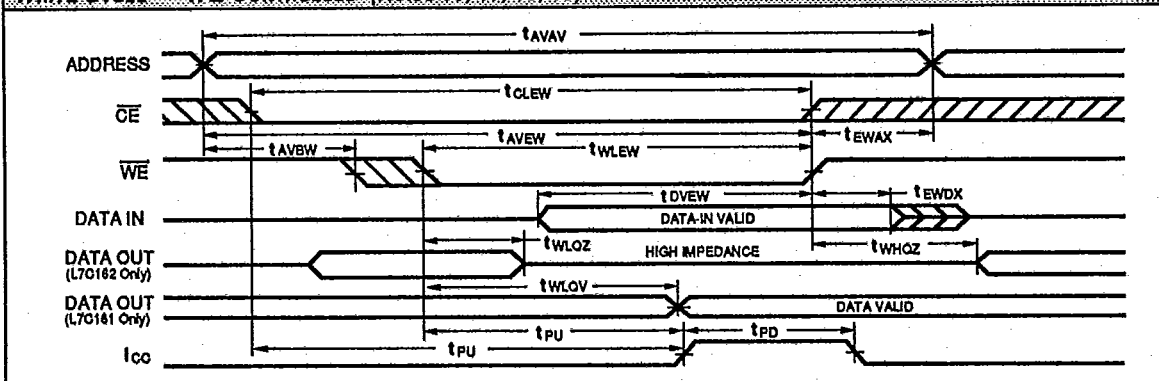


SWITCHING CHARACTERISTICS *Over Operating Range (ns)*

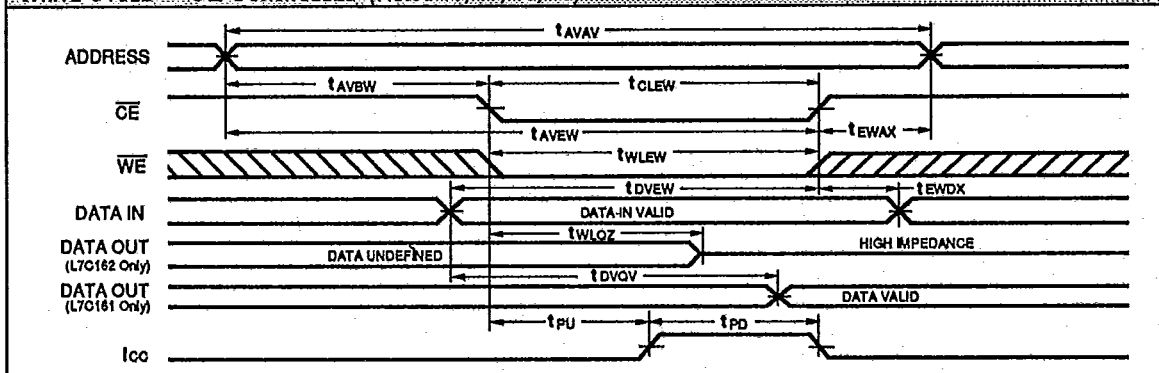
WRITE CYCLE (Notes 5, 11, 12, 22, 23, 24)

		L7C161/162-													
		35		25		20		15		12		10		8	
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
tAVAV	Write Cycle Time	25		20		20		15		12		10		8	
tCLEW	Chip Enable Low to End of Write Cycle	25		15		15		12		10		8		8	
tAVBW	Address Valid to Beginning of Write Cycle	0		0		0		0		0		0		0	
tAVEW	Address Valid to End of Write Cycle	25		15		15		12		10		8		8	
tEWAX	End of Write Cycle to Address Change	0		0		0		0		0		0		0	
tWLEW	Write Enable Low to End of Write Cycle	20		15		15		12		10		8		6.5	
tDVEW	Data Valid to End of Write Cycle	15		10		10		7		6		5		4	
tEWDX	End of Write Cycle to Data Change	0		0		0		0		0		0		0	
tWHOZ	Write Enable High to Output Low Z (20, 21)	0		0		0		0		0		0		0	
tWLOZ	Write Enable Low to Output High Z (20, 21)		10		7		7		5		4		4		3
tWLOV	Write Enable Low to Output Valid		30		20		15		15		12		10		8
tDVQV	Data Valid to Output Valid		30		20		15		15		12		10		8

WRITE CYCLE — WE CONTROLLED (Notes 16, 17, 18, 19)



WRITE CYCLE — CE CONTROLLED (Notes 16, 17, 18, 19)



NOTES

1. Maximum Ratings indicate stress specifications only. Functional operation of these products at values beyond those indicated in the Operating Conditions table is not implied. Exposure to maximum rating conditions for extended periods may affect reliability of the tested device.
2. The products described by this specification include internal circuitry designed to protect the chip from damaging substrate injection currents and accumulations of static charge. Nevertheless, conventional precautions should be observed during storage, handling, and use of these circuits in order to avoid exposure to excessive electrical stress values.
3. This product provides hard clamping of transient undershoot. Input levels below ground will be clamped beginning at -0.6 V. A current in excess of 100 mA is required to reach -2 V. The device can withstand indefinite operation with inputs as low as -3 V subject only to power dissipation and bond wire fusing constraints.
4. Duration of the output short circuit should not exceed 30 seconds.
5. A series of normalized curves on pages 2-8 through 2-11 of this data book supply the designer with typical DC and AC parametric information for Logic Devices Static RAMs. These curves may be used to determine device characteristics at various temperatures and voltage levels.
6. Tested with all address and data inputs changing at the maximum cycle rate. The device is continuously enabled for writing, i.e., $\overline{CE}1, \overline{WE} \leq V_{IL}$. Input pulse levels are 0 to 3.0 V.
7. Tested with outputs open and all address and data inputs changing at the maximum read cycle rate. The device is continuously disabled, i.e., $CE1$ or $CE2 \geq V_{IH}$.
8. Tested with outputs open and all address and data inputs stable. The device is continuously disabled, i.e., $CE1$ or $CE2 = V_{CC}$. Input levels are within 0.2 V of VCC or GND.
9. Data retention operation requires that VCC never drop below 2.0 V. $CE1$ or $CE2$ must be $\geq V_{CC} - 0.2$ V. For all other inputs $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V is required to ensure full powerdown.
10. These parameters are guaranteed but not 100% tested.
11. Test conditions assume input transition times of less than 3 ns, reference levels of 1.5 V, output loading for specified IOL and

- IOH plus 30 pF (Fig. 1a), and input pulse levels of 0 to 3.0 V (Fig. 2).
12. Each parameter is shown as a minimum or maximum value. Input requirements are specified from the point of view of the external system driving the chip. For example, t_{AVSW} is specified as a minimum since the external system must supply at least that much time to meet the worst-case requirements of all parts. Responses from the internal circuitry are specified from the point of view of the device. Access time, for example, is specified as a maximum since worst-case operation of any device always provides data within that time.
13. WE is high for the read cycle.
14. The chip is continuously selected ($CE1$ and $CE2$ low).
15. All address lines are valid prior to or coincident with the later of $CE1$ and $CE2$ transition to low.
16. The internal write cycle of the memory is defined by the overlap of $CE1, CE2$ low and WE low. All three signals must be low to initiate a write. Any signal can terminate a write by going high. The address, data, and control input setup and hold times should be referenced to the signal that falls last or rises first.
17. If WE goes low before or concurrent with the later of $CE1$ and $CE2$ going low, the output remains in a high impedance state.
18. If $CE1$ or $CE2$ goes high before or concurrent with WE going high, the output remains in a high impedance state.

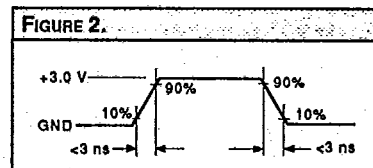
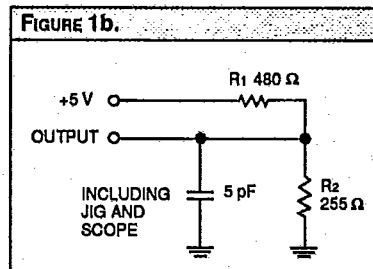
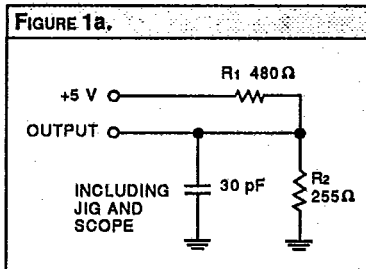
19. Powerup from ICC2 to ICC1 occurs as a result of any of the following conditions:
 - a. Falling edge of $\overline{CE}x$ (other \overline{CE} active).
 - b. Falling edge of WE ($\overline{CE}1, \overline{CE}2$ active).
 - c. Transition on any address line ($CE1, CE2$ active).
 - d. Transition on any data line ($CE1, CE2$, and WE active).

The device automatically powers down from ICC2 to ICC1 after t_{PD} has elapsed from any of the prior conditions. This means that power dissipation is dependent on only cycle rate, and is not on Chip Select pulse width.

20. At any given temperature and voltage condition, output disable time is less than output enable time for any given device.

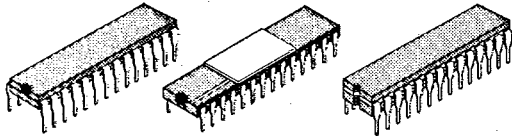
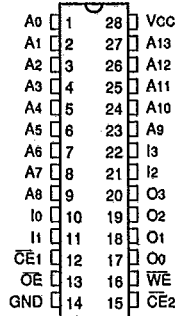
21. Transition is measured ± 200 mV from steady state voltage with specified loading in Fig. 1b. This parameter is sampled and not 100% tested.
22. All address timings are referenced from the last valid address line to the first transitioning address line.
23. $\overline{CE}1, \overline{CE}2$, or WE must be high during address transitions.
24. This product is a very high speed device and care must be taken during testing in order to realize valid test information. Inadequate attention to setups and procedures can cause a good part to be rejected as faulty. Long high inductance leads that cause supply bounce must be avoided by bringing the VCC and ground planes directly up to the contactor fingers. A 0.01 μ F high frequency capacitor is also required between VCC and ground. To avoid signal reflections, proper terminations must be used.

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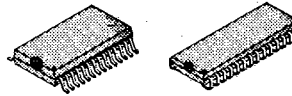
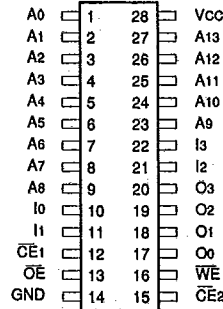


ORDERING INFORMATION

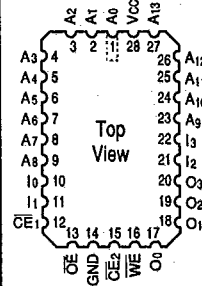
28-pin
(0.3" wide)



28-pin



28-pin
(350 x 550)



Speed	Plastic DIP (P10)	Sidebraze Hermetic DIP (D10)	CerDIP (C5)	Plastic SOIC (.300" - U2)	Plastic SOJ (.300" - W2)	Ceramic Leadless Chip Carrier (K5)
0°C to +70°C — COMMERCIAL SCREENING						
35 ns 25 ns 20 ns 15 ns 12 ns 10 ns 8 ns	L7C161PC or L7C162PC	L7C161DC or L7C162DC	L7C161CC or L7C162CC	L7C161UC or L7C162UC	L7C161WC or L7C162WC	L7C161KC or L7C162KC
-55°C to +125°C — COMMERCIAL SCREENING						
35 ns 25 ns 20 ns 15 ns 12 ns 10 ns 8 ns		L7C161DM or L7C162DM	L7C161CM or L7C162CM			L7C161KM or L7C162KM
-55°C to +125°C — EXTENDED SCREENING						
35 ns 25 ns 20 ns 15 ns 12 ns 10 ns 8 ns		L7C161DME or L7C162DME	L7C161CME or L7C162CME			L7C161KME or L7C162KME
-55°C to +125°C — MIL-STD-883 COMPLIANT						
35 ns 25 ns 20 ns 15 ns 12 ns 10 ns 8 ns		L7C161DMB or L7C162DMB	L7C161CMB or L7C162CMB			L7C161KMB or L7C162KMB

